FORM PTO-1449 (Modified)	Docket No. 378-21-034	Application Number 10/655,904
INFORMATION DISCLOSURE CITATION IN AN APPLICATION	Applicant James D. Parsons	
(Use several sheets if necessary)	Filing Date	Group Art Unit 2878

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
OG	6 2 3 9 4 3 2	05-2001	Parsons	250	338.1	
OG	5 1 2 2 6 6 8	06-1992	Kajiwara et al.	338	18	
OG	5 8 6 8 4 9 7A	02-1999	Jung	374	179	
OG	5 0 2 5 2 4 3A	06-1991	Ichikawa	338	19	
OG	4 6 9 5 7 3 3A	09-1987	Pesavento	250	551	

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

OG	1.	DE VASCONCELOS E A ET AL: "Highly sensitive thermistors based on high-purity polycrystalline cubic silicon carbide" SENSORS AND ACTUATORS A, ELSEVIER SEQUOIA S.A., LAUSANNE, CH, Vol. 83, no. 1-3, May 2000 (2000-05), pages 167-171, XP004198310 ISSN: 0924-4247
OG	2	DE VASCONCELOS E A ET AL: "Potential of high-purity polycrystalline silicon carbide for thermistor applications" JAPANESE JOURNAL OF APPLIED PHYSICS, PART 1 (REGULAR PAPERS, SHORT NOTES & REVIEW PAPERS), SEPT. 1998, PUBLICATION OFFICE, JAPANESE JOURNAL APPL. PHYS, JAPAN, vol. 37, no. 9A, pages 5078-5079, XP002211060 ISSN: 0021-4922
OG	3	Materials for High Temperature Semiconductor Devices: Committee on Materials for High-Temperature Semiconductor Devices, National Materials Advisory Board, Commission on Engineering and Technical Systems, National Research Council: National Academy Press, Washington, D.C., 1995, pp.68-70.
OG	4	O. Nennewitz, L. Spiess and V. Breternitz, "Ohmic Contacts to 6H-SiC", Applied Surface Science, Vol. 91, 1995, pages 347-351.
OG	5	J.A. Lely and P.A. Kroeger, "Electrical Properties of Hexagonal SiC Doped with N, B or Al", In Semiconductors and Phosphors, Proceedings of Intl. Colloquium-Partenkirchen, Ed. M. Schoen and H. Welker, New York, Interscience Pub., Inc. 1958, pp. 525-533.
OG	6	Q.Y. Tong, U. Gosele, C. Yuan, A.J. Stecki & M. Reiche, "Silicon Carbide Wafer Bonding", J. Electrochem Soc., Vol. 142, No. 1, January 1995, pp. 232-236.

Examiner	Date Considered
[signature]	05/02/05

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FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

OG	7	Choyke,W.J., "Optical and Electronic Properties of SiC" NATO ASI Series Vol. "The Physics and Chemistry of Carbides, Nitrides and Borides", Manchester, England, pp. 1-25, 9/18-22,1999
OG	8	Spitzer et al., "Infrared Properties of Hexagonal Silicon Carbide", Physical Review, Vo. 113, No. 1, pp. 127-132, January 1, 1959.
OG	9	Electronic Properties Information Center, "Silicon Carbide", Hughes Aircraft Company, June 1965, pp. 9-16.
OG	10	P.K. Bhattacharya, "Bonding of SiC Slabs for Electro-Mechanical Heat-Sinks in Advanced Packaging Applications", J. Electronics, Vol. 73, No. 1, 1992, pp. 71-83.
OG	11	Westinghouse Astronuclear Laboratory "Silicon Carbide Junction Thermistor", 1965
OG	12	Jeffrey B. Casady et al, "A Hybrid 6H-Sic temperature Sensor Operational from 25°C to 500°C, IEEE Transactions on Components, Packaging and Manufacturing Technology" - Part A, Vol. 19, No. 3 (September 1996, pp 416-422.

Examiner	Date Considered
Olik Chaudhuri	03/25/05

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Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation	
						Yes	No

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

OG	13	Takashi Nagel and Masahiko Itch, "Sic Thin-Film Thermistors", IEEE Transactions on Industry Applications, Vol. 26, No. 6, November/December 1990, pp. 1139-1143.1
OG	14	"Electrical Properties of β-Sic Heavily Doped with Nitrogen" O. A. Golikova, L.M. Ivanova, A. A. Pletyushkin, and V.P. Semenenko, A.A. Balkov Institute of Metallurgy, Academy of Sciences of the USSR, Moscow Institute of Semiconductors, Academy of Sciences of the USSR, Leningrad Translated from Fizika I Tehnika Poluprovodnikov, Vol. 5, No. 3, pp. 417-420, March 1971, Original article submitted May 26, 1970; revision submitted July 8, 1970.
OG	15	"Galvanomagnetic Effects in n-type Silicon Carbide at Low Temperatures", M.I. Iglitsyn, M. Mirzabaev, V.M. Tuchkevich, E.F. Fedomova, and Yu. V. Shmartsev, A.F. Ioffe Physicotechnical Institute, Academy of Sciences, USSR, Leningrad State Research and Planning Institute for the Rare Metal Industry, Moscow, Translated from fizika Tverdogo Tela, Vol. 6, No. 9, pp. 2673-2682, September, 1964, Originak article submitted March 31, 1964

Examiner	Date Considered
Olek Galan	03/25/05

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